

In the Claims

Kindly amend claims 1, 4, 5 and 7 to read as follows:

1. (Trice amended) A method of fabricating an oxide-nitride-oxide (ONO) layer in a memory cell, said method comprising:
- forming a bottom oxide layer on a substrate;
- depositing a nitride layer; and
- oxidizing a top oxide layer, thereby causing oxygen to be introduced into substantially all of said nitride layer within said memory cell, so as to enhance charge localization within said nitride layer.
4. (Trice amended) A method for improving the charge retention in a nitride layer of a memory cell, said method comprising:
- depositing a nitride layer; and
- introducing oxygen into substantially all of said nitride layer within said memory cell, so as to enhance charge localization within said nitride layer.
5. (Trice amended) A method for improving the charge retention in a nitride layer of a memory cell, said method comprising:
- depositing a nitride layer;
- controlling the thickness of said deposited nitride layer; and
- introducing oxygen into substantially all of said nitride layer within said memory cell, so as to enhance charge localization within said nitride layer.
7. (Twice amended) A method of manufacturing a programmable, read only memory device, the method comprising:
- forming a first oxide layer on a substrate,
- forming a nitride layer on top of said oxide layer, wherein said nitride layer is 150 angstroms or less thick;
- introducing oxygen into substantially all of said nitride layer within a memory cell during formation of a second oxide layer on top of said nitride layer, so as to enhance charge localization within said nitride layer;

D³
cont.

patterning said oxide-nitride-oxide (ONO) layers into desired patterns; and
forming a gate layer over said patterned ONO layer.